

ABSTRACT

A semiconductor device is provided. The semiconductor device includes insulating isolation patterns each including a void, semiconductor patterns respectively stacked on the insulating isolation patterns, gate structures respectively extending around the semiconductor patterns, first and second source/drain patterns respectively connected to opposing sides of the plurality of semiconductor patterns in a first direction, an active contact structure extending between insulating isolation patterns adjacent to the first source/drain pattern and connected to the first source/drain pattern, a dummy contact structure extending between the insulating isolation patterns adjacent to the second source/drain pattern and electrically isolated from the second source/drain pattern, and an interconnection line on lower surfaces of the insulating isolation patterns, electrically connected to the active contact structure, and electrically isolated from the dummy contact structure.

FIG. 2